FDP10N50F / FDPF10N50FT

N-Channel MOSFET

500V, 9A, 0.85Ω

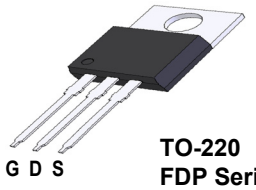
Features

- $R_{DS(on)}$ = 0.71Ω (Typ.) @ V_{GS} = 10V, I_D = 4.5A
- Low Gate Charge (Typ. 18nC)
- Low C_{rss} (Typ. 10pF)
- Fast Switching
- 100% Avalanche Tested
- Improved dv/dt Capability
- RoHS Compliant

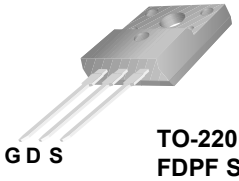
Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

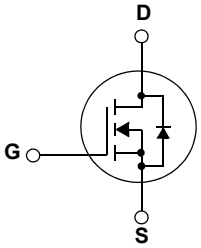
This advance technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switching mode power supplies and active power factor correction.



TO-220
FDP Series



TO-220F
FDPF Series



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol	Parameter			FDP10N50F	FDPF10N50FT	Units
V_{DSS}	Drain to Source Voltage			500		V
V_{GSS}	Gate to Source Voltage			±30		V
I_D	Drain Current	-Continuous (T_C = 25°C)		9	9*	A
		-Continuous (T_C = 100°C)		5.4	5.4*	
I_{DM}	Drain Current	- Pulsed	(Note 1)	36	36*	A
E_{AS}	Single Pulsed Avalanche Energy		(Note 2)	364		mJ
I_{AR}	Avalanche Current		(Note 1)	9		A
E_{AR}	Repetitive Avalanche Energy		(Note 1)	12.5		mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	20		V/ns
P_D	Power Dissipation	(T_C = 25°C)		125	42	W
		- Derate above 25°C		1.0	0.33	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range			-55 to +150		°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300		°C

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FDP10N50F	FDPF10N50FT	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.0	3.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	62.5	

Package Marking and Ordering Information $T_C = 25^oC$ unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP10N50F	FDP10N50F	TO-220	-	-	50
FDPF10N50FT	FDPF10N50FT	TO-220F	-	-	50

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu A$, $V_{GS} = 0V$, $T_J = 25^oC$	500	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$, Referenced to 25^oC	-	0.5	-	$V/^oC$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500V$, $V_{GS} = 0V$	-	-	10	μA
		$V_{DS} = 400V$, $T_C = 125^oC$	-	-	100	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30V$, $V_{DS} = 0V$	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu A$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10V$, $I_D = 4.5A$	-	0.71	0.85	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 20V$, $I_D = 4.5A$ (Note 4)	-	8.5	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, f = 1MHz	-	880	1170	pF
C_{oss}	Output Capacitance		-	120	160	pF
C_{rss}	Reverse Transfer Capacitance		-	10	15	pF
Q_g	Total Gate Charge at 10V	$V_{DS} = 400V$, $I_D = 10A$, $V_{GS} = 10V$ (Note 4, 5)	-	18	24	nC
Q_{gs}	Gate to Source Gate Charge		-	5	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	7.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250V$, $I_D = 10A$, $R_G = 25\Omega$ (Note 4, 5)	-	20	50	ns
t_r	Turn-On Rise Time		-	40	90	ns
$t_{d(off)}$	Turn-Off Delay Time		-	45	100	ns
t_f	Turn-Off Fall Time		-	30	70	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	9	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	60	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V$, $I_{SD} = 9A$	-	-	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0V$, $I_{SD} = 9A$, $dI_F/dt = 100A/\mu s$ (Note 4)	-	95	-	ns
Q_{rr}	Reverse Recovery Charge		-	0.2	-	μC

Notes:
1: Repetitive Rating: Pulse width limited by maximum junction temperature
2: L = 9mH, $I_{AS} = 9A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25°C$
3: $I_{SD} \leq 8A$, $di/dt \leq 200A/\mu s$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25°C$
4: Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5: Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

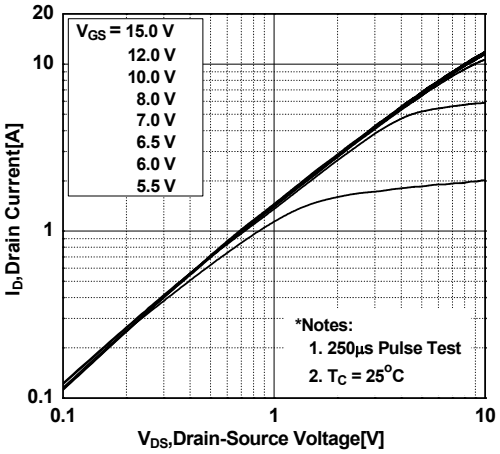


Figure 2. Transfer Characteristics

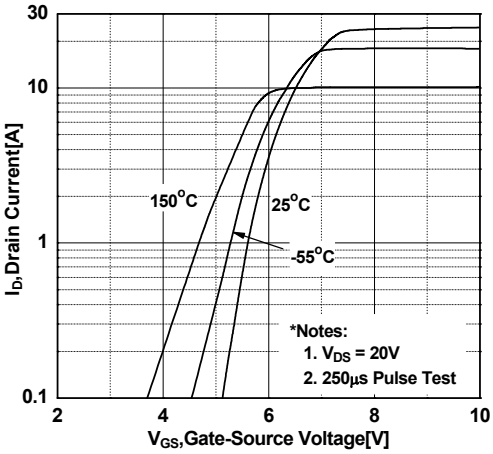


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

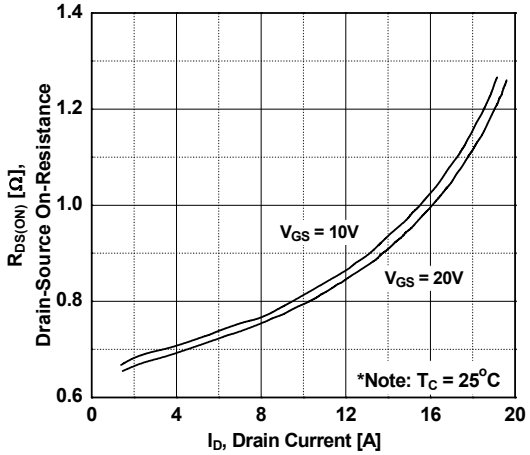


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

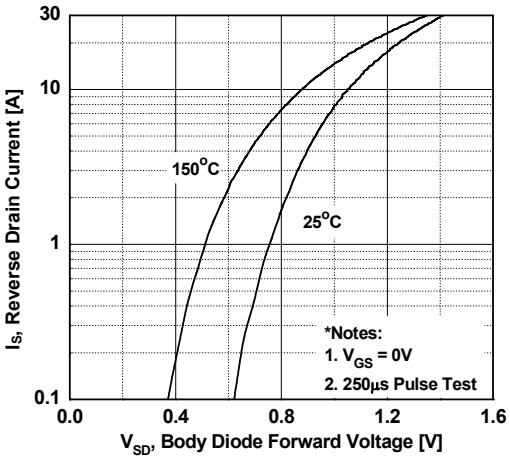


Figure 5. Capacitance Characteristics

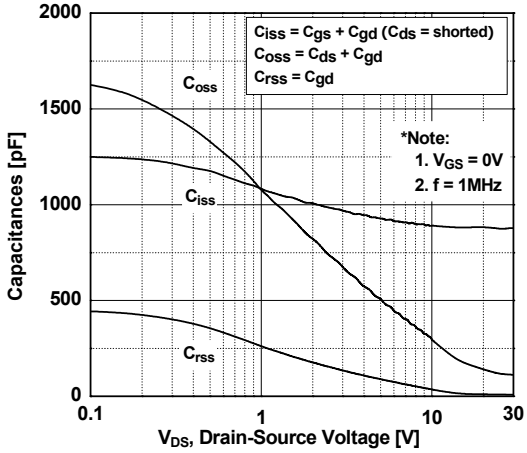


Figure 6. Gate Charge Characteristics